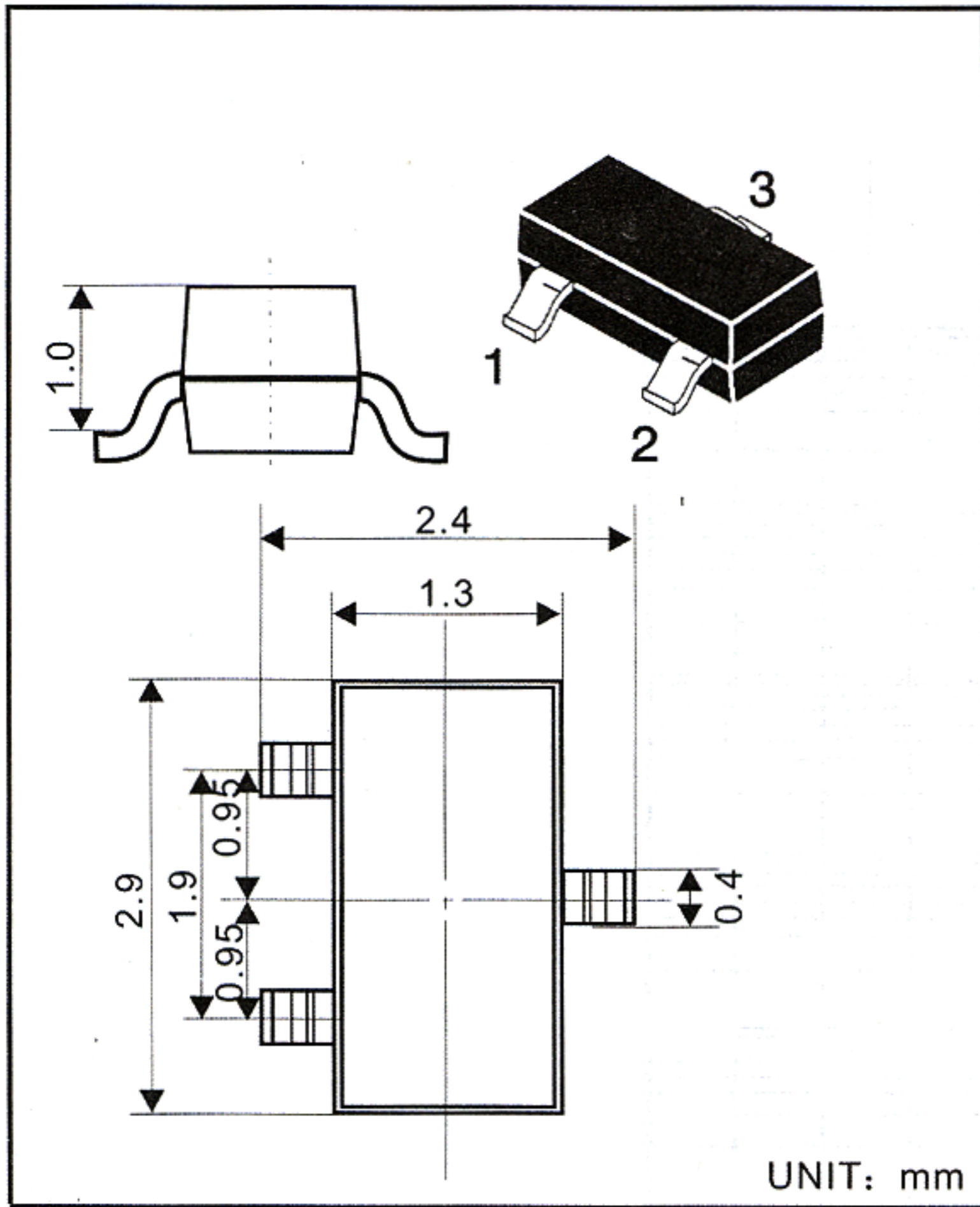


BAS40 SERIES SCHOTTKY DIODE



FEATURES

Power dissipation

P_D : 200mW ($T_{amb}=25^\circ C$)

Forward current

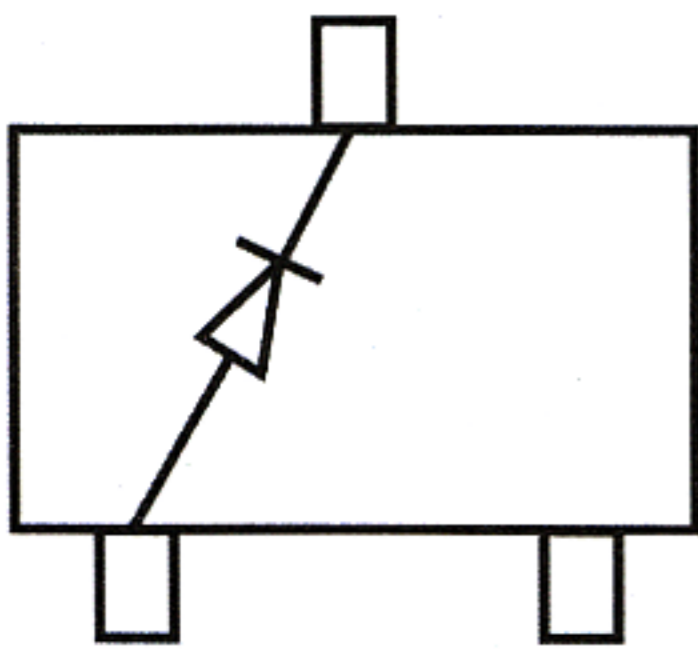
I_F : 200mA

Reverse voltage

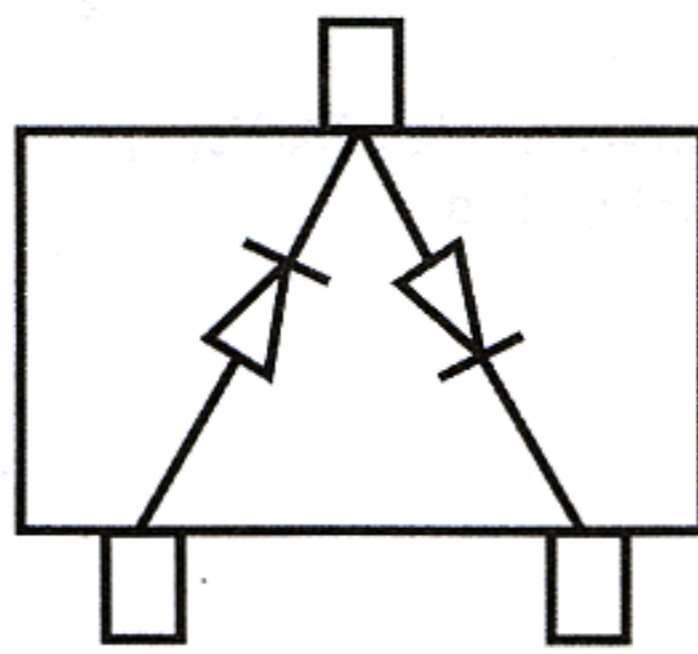
V_R : 40V

Operating and storage junction temperature range

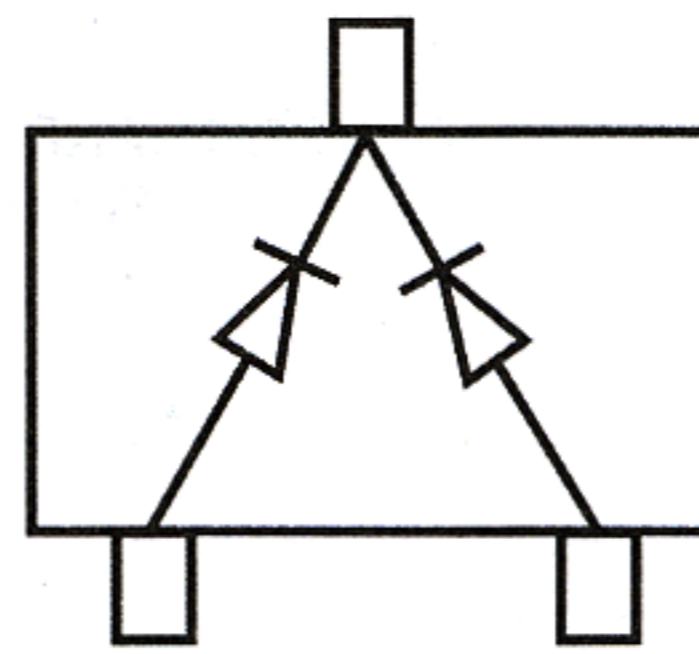
T_J, T_{stg} : $-55^\circ C$ to $+150^\circ C$



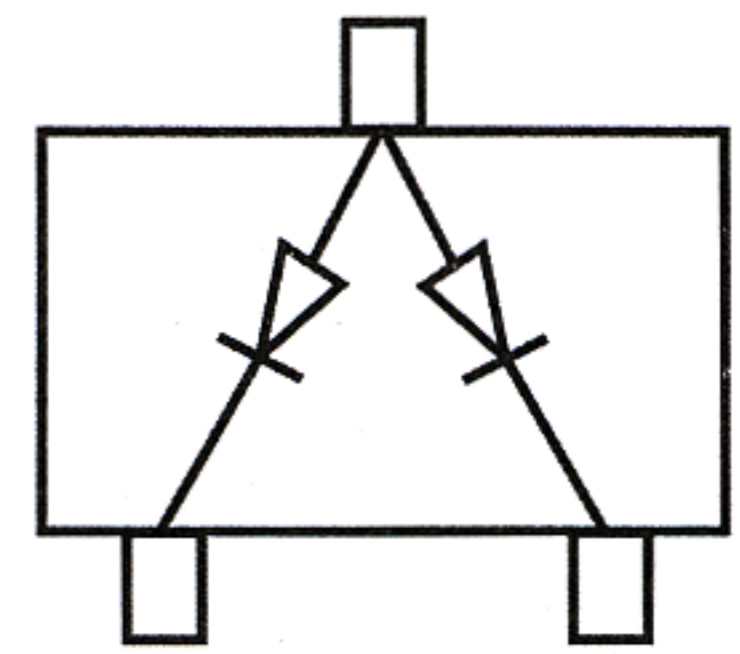
BAS40 MARKING: 43



BAS40-04 MARKING: 44



BAS40-05 MARKING: 45



BAS40-06 MARKING: 46

ELECTRICAL CHARACTERISTICS

($T_{amp}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100 \mu A$	40		V
Reverse voltage leakage current	I_R	$V_R=30V$		2	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=40mA$		380 1000	mV
Diode capacitance	C_{tot}	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$		5	ns

